NEC

PNP SILICON TRANSISTOR 2SA954

DESCRIPTION

The 2SA954 is designed for use in driver stage of high voltage

audio equipment.

FEATURES

• High total power dissipation.

 $P_T = 600 \text{ mW}$

• High hee and high voltage.

 $h_{FE} (I_C = -50 \text{ mA}) : 200 \text{ TYP.}$ $V_{CEO} : -80 \text{ V}$

ABSOLUTE MAXIMUM RATINGS

Maximum Temperatures

PACKAGE DIMENSIONS in millimeters (inches) 5.2 MAX. (0.204 MAX.) 0.45 (0.10) 1.27 (0.05) 1.27 (0.05) 1.27 (0.05) 1.27 (0.05) 1.27 (0.05) 1.28 2.43 3. BASE EIAJ : SC-43B JEDEC: TO-92 IEC : PA33

ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
hfE1*	DC Current Gain	90	200	400	_	V _{CE} =-1.0 V, I _C =-50 mA
hFE2*	DC Current Gain	30	80 .		_	$V_{CE} = -1.0 \text{ V, } I_{C} = -300 \text{ mA}$
Cob	Collector to Base Capacitance		13	25	pF	$V_{CB} = -6.0 \text{ V, IE} = 0$ f = 1.0 MHz
fT	Gain Bandwidth Product	50	100		MHz	$V_{CE} = -6.0 \text{ V, I}_{E} = 10 \text{ mA}$
VBE*	Base to Emitter Voltage	-600	-660	-700	mV	$V_{CE} = -6.0 \text{ V, I}_{C} = -10 \text{ mA}$
VCE(sat)*	Collector Saturation Voltage		-0.15	-0.6	V	$1_{C} = -300 \text{ mA}, 1_{B} = -30 \text{ mA}$
VBE(sat)*	Base Saturation Voltage		-0.85	-1.2	. v	IC=-300 mA, IB=-30 mA
Ісво	Collector Cutoff Current			-100	nA	$V_{CB} = -80 \text{ V, } I_{E} = 0$
IEBO	Emitter Cutoff Current			-100	nA	V _{EB} =-5.0 V, I _C =0

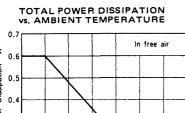
^{*} Pulsed PW \leq 350 μ s, duty cycle \leq 2.0 %

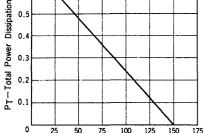
Classification of hee1

Rank	M	L	K
Range	90 – 180	135 — 270	200 – 400

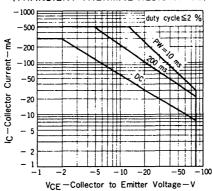
hFE Test Conditions : $V_{CE} = -1.0 \text{ V}$, $I_{C} = -50 \text{ mA}$

TYPICAL CHARACTERISTICS (Ta = 25 °C unless otherwise noted)

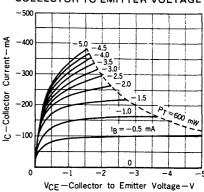




SAFE OPERATING AREAS (TRANSIENT THERMAL RESISTANCE)

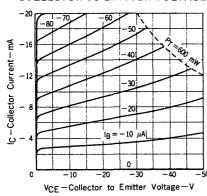


COLLECTOR CURRENT vs.
COLLECTOR TO EMITTER VOLTAGE

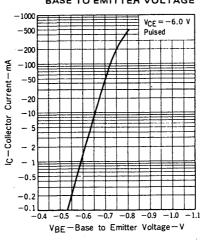




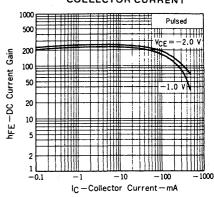
Ta-Ambient Temperature-°C



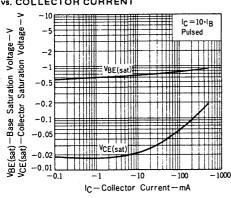
COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE



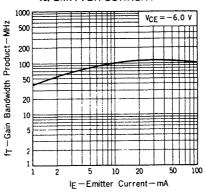
DC CURRENT GAIN vs. COLLECTOR CURRENT



BASE AND COLLECTOR SATURATION VOLTAGE VS. COLLECTOR CURRENT



GAIN BANDWIDTH PRODUCT vs. EMITTER CURRENT



EMITTER TO BASE AND COLLECTOR TO BASE CAPACITANCE vs. REVERSE VOLTAGE

